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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HD74HC258

Quad. 2-to-1-line Data Selectors/Multiplexers (with 3-state outputs)



ADE-205-479 (Z)
1st. Edition
Sep. 2000

Description

The large output drive capability coupled with the 3-state feature make this device ideal for interfacing with bus lines in a bus organized system. When the output control input line is taken high, the outputs of all four multiplexers are sent into a high impedance state. When the output control line is low, the select input chooses whether the A or B input is used.

Features

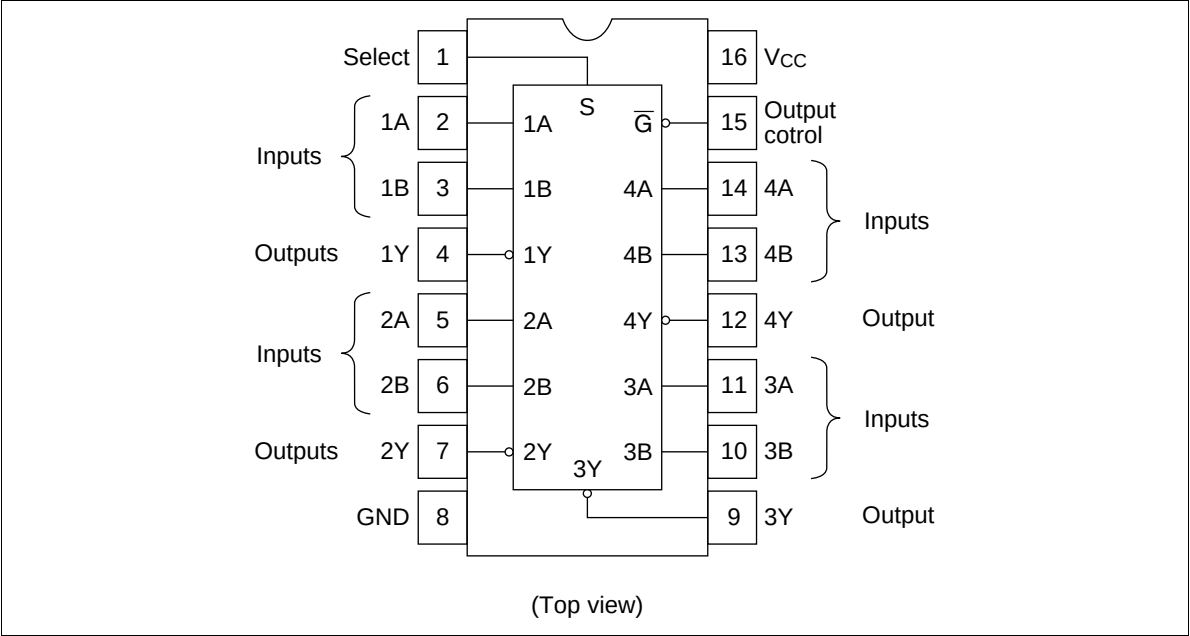
- High Speed Operation: t_{pd} (Data to Y) = 11 ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2$ to 6 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)

Function Table

Inputs		Outputs		
Output Control	Select	A	B	Y
H	X	X	X	Z
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

Notes H: high level
L: low level
X: irrelevant
Z: off (high-impedance) state of a 3-state output

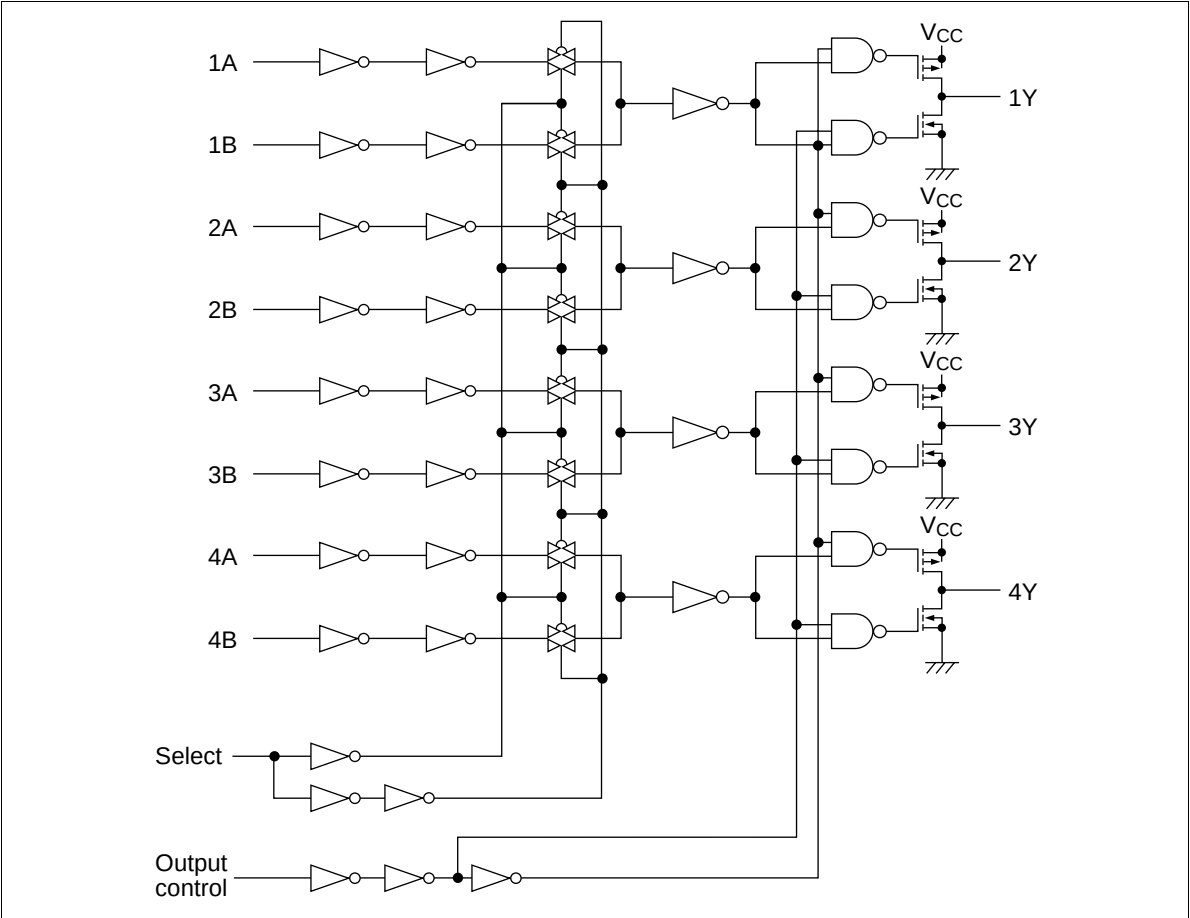
Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
DC current drain per pin	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC}, I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	-65 to +150	°C

Logic Diagram



DC Characteristics

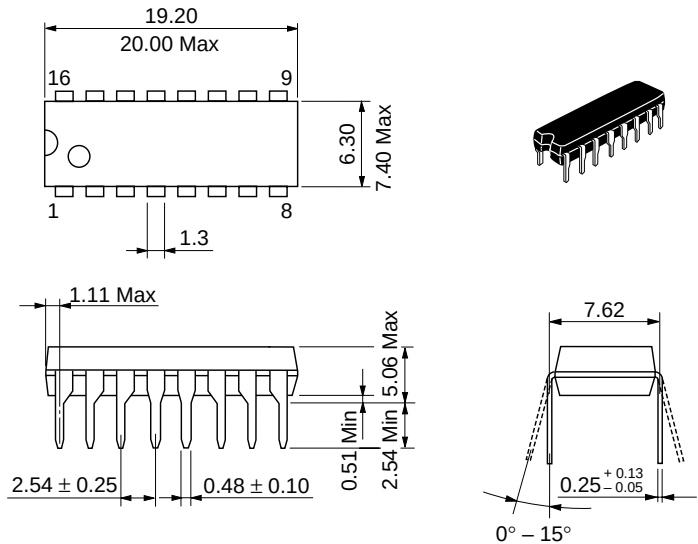
Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	μA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA	Vin = V _{CC} or GND, Iout = 0 μA	

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Item	Symbol	V _{CC} (V)	Ta = 25°C		Ta = −40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min			Max
Propagation delay time	t _{PLH}	2.0	—	—	115	—	145	ns	Data to Y
	t _{PHL}	4.5	—	11	23	—	29		Select to Y
		6.0	—	—	20	—	25		
		2.0	—	—	115	—	145		
		4.5	—	13	23	—	29		
		6.0	—	—	20	—	25		
Output enable time	t _{ZL}	2.0	—	—	150	—	190	ns	
		4.5	—	11	30	—	38		
		6.0	—	—	26	—	33		
	t _{ZH}	2.0	—	—	150	—	190	ns	
		4.5	—	13	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t _{LZ}	2.0	—	—	150	—	190	ns	
		4.5	—	13	30	—	38		
		6.0	—	—	26	—	33		
	t _{HZ}	2.0	—	—	150	—	190	ns	
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t _{TLH}	2.0	—	—	60	—	75	ns	
	t _{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C _{in}	—	—	5	10	—	10	pF	

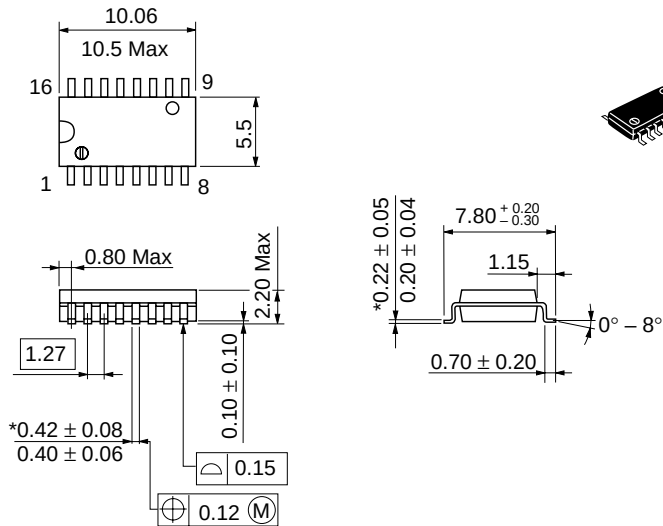
Package Dimensions

Unit: mm



Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.07 g

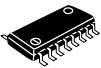
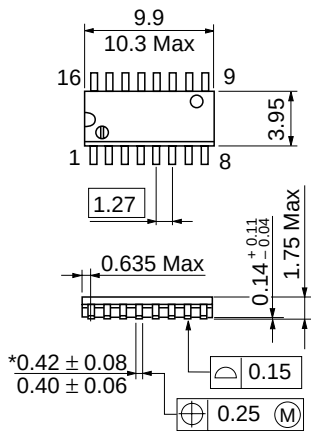
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.24 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.15 g

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